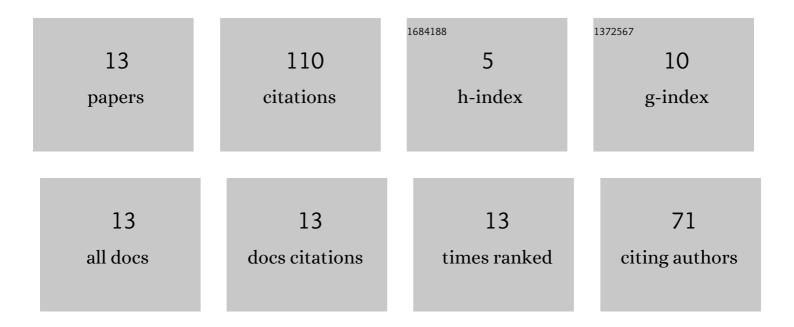
## Rafik M Imamov

List of Publications by Year in descending order

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#	Article	IF	CITATION
1	Asymmetric X-Ray Diffraction. Crystallography Reviews, 1992, 3, 157-226.	1.5	42
2	Metamorphic InAlAs/InGaAs/InAlAs/GaAs HEMT heterostructures containing strained superlattices and inverse steps in the metamorphic buffer. Journal of Crystal Growth, 2013, 366, 55-60.	1.5	23
3	Structural and electrical properties of quantum wells with nanoscale InAs inserts in In y Al1 â՞ y As/In x Ga1 â՞ x As heterostructures on InP substrates. Crystallography Reports, 2011, 56, 298-309.	0.6	11
4	Study of new designs for the InAlAs metamorphic buffer on GaAs substrates with distributed compensation of elastic deformations. Semiconductors, 2013, 47, 997-1002.	0.5	8
5	X-Ray diffractometry of metamorphic nanoheterostructures. Crystallography Reports, 2014, 59, 258-265.	0.6	8
6	<title>Structural diagnostics of quantum layers by x-ray diffraction and standing waves</title> . , 2004, 5401, 543.		5
7	Study of the influence of strained superlattices introduced into a metamorphic buffer on the electrophysical properties and the atomic structure of InAlAs/InGaAs MHEMT heterostructures. Semiconductors, 2013, 47, 532-537.	0.5	4
8	Structural and electrical properties of InAlAs/InGaAs/InAlAs HEMT heterostructures on InP substrates with InAs inserts in quantum well. Crystallography Reports, 2014, 59, 900-907.	0.6	3
9	Structural characterization of interfaces in the AlxGa1â^'x As/GaAs/AlxGa1â^'x As heterostructures by high-resolution X-ray reflectometry and diffractometry. Crystallography Reports, 2005, 50, 739-750.	0.6	2
10	Electrical and structural characteristics of metamorphic In0.38Al0.62As/In0.37Ga0.63As/In0.38Al0.62As HEMT nanoheterostructures. Crystallography Reports, 2013, 58, 914-919.	0.6	2
11	Electrophysical characteristics and structural parameters of metamorphic HEMT nanoheterostructures In0.7Al0.3As/In0.7Ga0.3As/In0.7Al0.3As containing superlattices with different numbers of periods in the metamorphic buffer. Crystallography Reports, 2014, 59, 425-429.	0.6	2
12	Study of the relationship between the crystal structure of nanolayers and electrical properties in Al x Ga1â^'x As/In y Ga1â^'y As pseudobinary heterostructures by double-crystal X-ray diffraction. Crystallography Reports, 2008, 53, 183-186.	0.6	0
13	The electrical and structural properties of In y Ga1 â^' y As/In x Al1 â^' x As/InP quantum wells with different InAs content. Crystallography Reports, 2010, 55, 6-9.	0.6	0